Lattice Semiconductor Corporation - LFE3-95EA-6LFN484I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	295
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95ea-6lfn484i

PLL/DLL Cascading

LatticeECP3 devices have been designed to allow certain combinations of PLL and DLL cascading. The allowable combinations are:

- PLL to PLL supported
- PLL to DLL supported

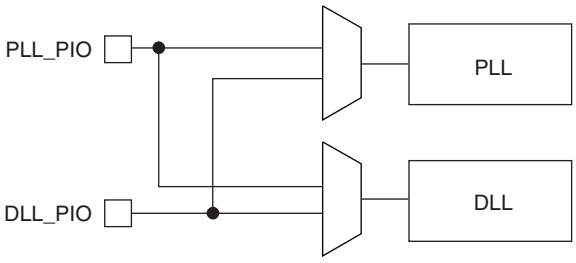
The DLLs in the LatticeECP3 are used to shift the clock in relation to the data for source synchronous inputs. PLLs are used for frequency synthesis and clock generation for source synchronous interfaces. Cascading PLL and DLL blocks allows applications to utilize the unique benefits of both DLLs and PLLs.

For further information about the DLL, please see the list of technical documentation at the end of this data sheet.

PLL/DLL PIO Input Pin Connections

All LatticeECP3 devices contains two DLLs and up to ten PLLs, arranged in quadrants. If a PLL and a DLL are next to each other, they share input pins as shown in the Figure 2-7.

Figure 2-7. Sharing of PIO Pins by PLLs and DLLs in LatticeECP3 Devices



Note: Not every PLL has an associated DLL.

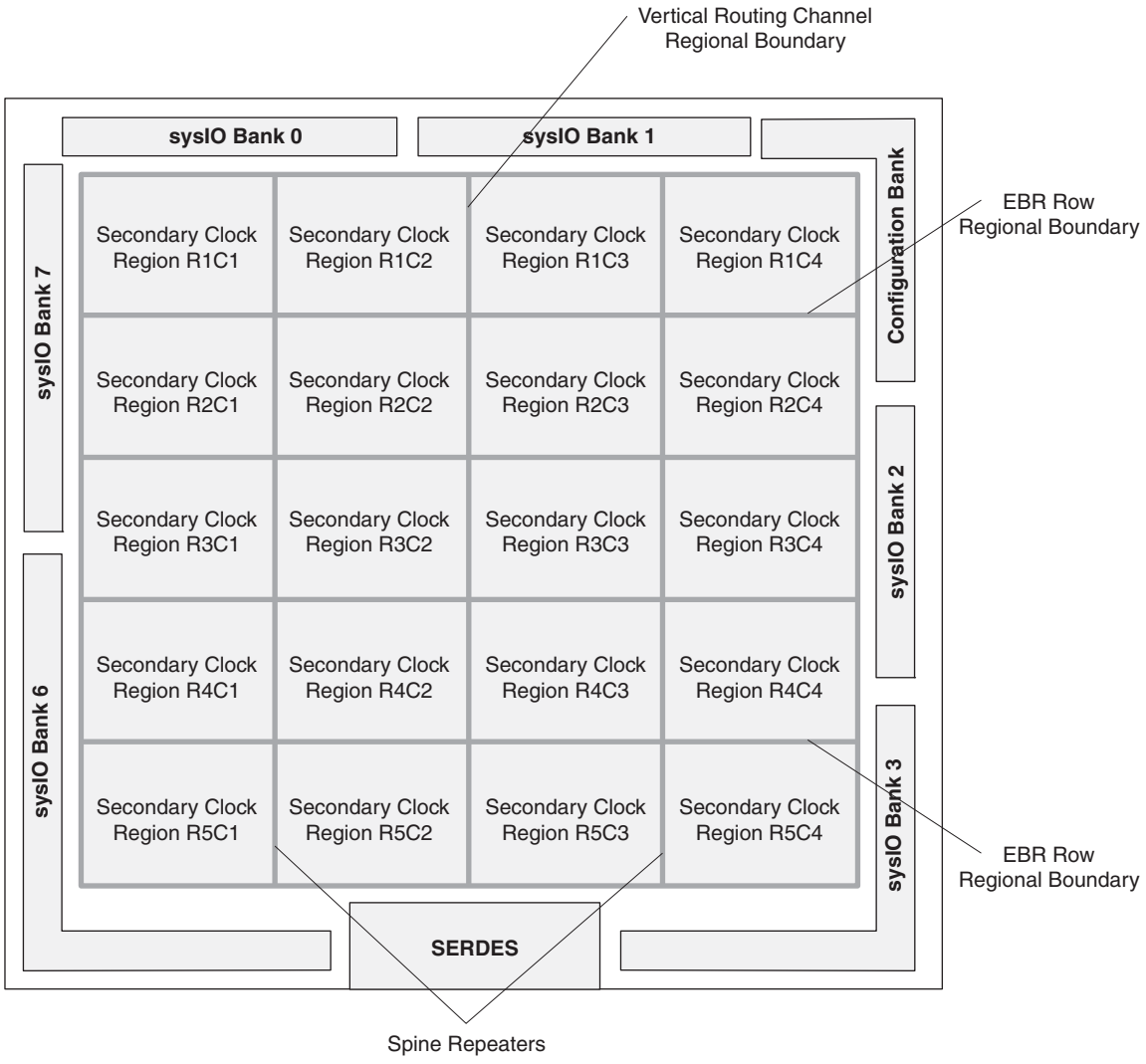
Clock Dividers

LatticeECP3 devices have two clock dividers, one on the left side and one on the right side of the device. These are intended to generate a slower-speed system clock from a high-speed edge clock. The block operates in a ÷2, ÷4 or ÷8 mode and maintains a known phase relationship between the divided down clock and the high-speed clock based on the release of its reset signal. The clock dividers can be fed from selected PLL/DLL outputs, the Slave Delay lines, routing or from an external clock input. The clock divider outputs serve as primary clock sources and feed into the clock distribution network. The Reset (RST) control signal resets input and asynchronously forces all outputs to low. The RELEASE signal releases outputs synchronously to the input clock. For further information on clock dividers, please see TN1178, LatticeECP3 sysCLOCK PLL/DLL Design and Usage Guide. Figure 2-8 shows the clock divider connections.

Table 2-6. Secondary Clock Regions

Device	Number of Secondary Clock Regions
ECP3-17	16
ECP3-35	16
ECP3-70	20
ECP3-95	20
ECP3-150	36

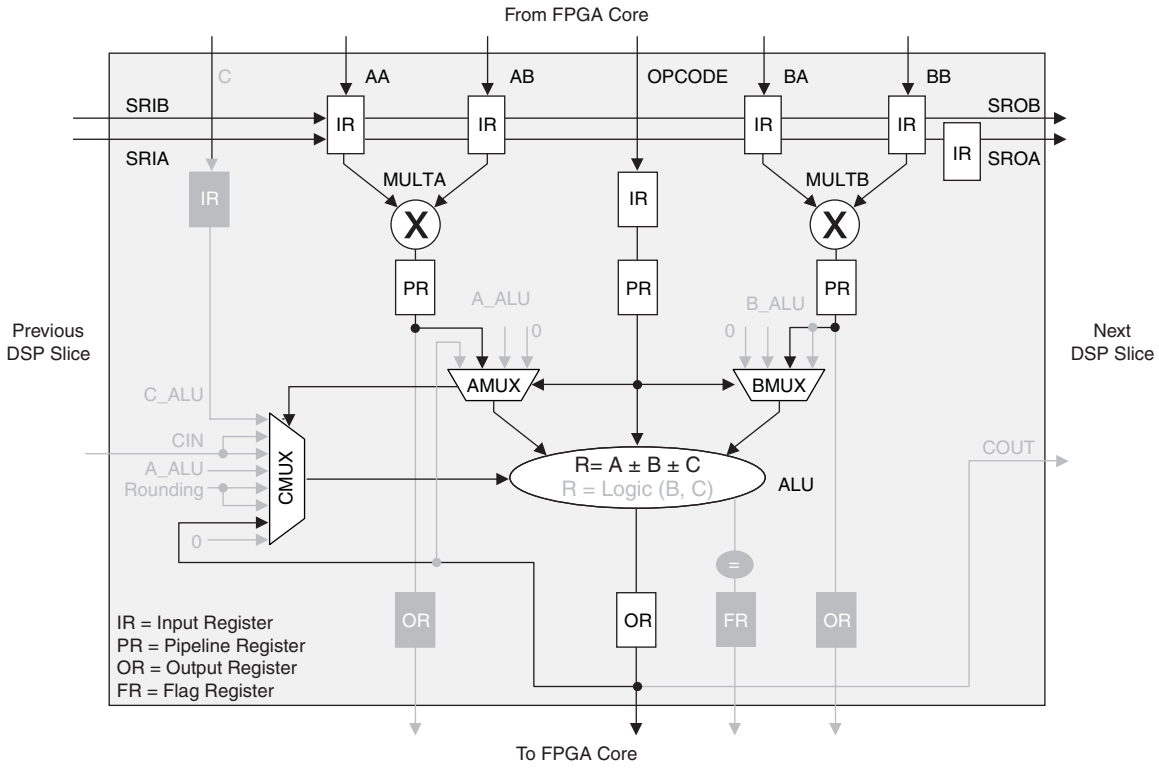
Figure 2-15. LatticeECP3-70 and LatticeECP3-95 Secondary Clock Regions



MMAC DSP Element

The LatticeECP3 supports a MAC with two multipliers. This is called Multiply Multiply Accumulate or MMAC. In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value and with the result of the multiplier operation of operands BA and BB. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-28 shows the MMAC sysDSP element.

Figure 2-28. MMAC sysDSP Element



Two adjacent PIOs can be joined to provide a differential I/O pair (labeled as “T” and “C”) as shown in Figure 2-32. The PAD Labels “T” and “C” distinguish the two PIOs. Approximately 50% of the PIO pairs on the left and right edges of the device can be configured as true LVDS outputs. All I/O pairs can operate as LVDS inputs.

Table 2-11. PIO Signal List

Name	Type	Description
INDD	Input Data	Register bypassed input. This is not the same port as INCK.
IPA, INA, IPB, INB	Input Data	Ports to core for input data
OPOSA, ONEGA[1], OPOSB, ONEGB[1]	Output Data	Output signals from core. An exception is the ONEGB port, used for tristate logic at the DQS pad.
CE	PIO Control	Clock enables for input and output block flip-flops.
SCLK	PIO Control	System Clock (PCLK) for input and output/TS blocks. Connected from clock ISB.
LSR	PIO Control	Local Set/Reset
ECLK1, ECLK2	PIO Control	Edge clock sources. Entire PIO selects one of two sources using mux.
ECLKDQSR[1]	Read Control	From DQS_STROBE, shifted strobe for memory interfaces only.
DDRCLKPOL[1]	Read Control	Ensures transfer from DQS domain to SCLK domain.
DDRLAT[1]	Read Control	Used to guarantee INDDRX2 gearing by selectively enabling a D-Flip-Flop in datapath.
DEL[3:0]	Read Control	Dynamic input delay control bits.
INCK	To Clock Distribution and PLL	PIO treated as clock PIO, path to distribute to primary clocks and PLL.
TS	Tristate Data	Tristate signal from core (SDR)
DQCLK0[1], DQCLK1[1]	Write Control	Two clocks edges, 90 degrees out of phase, used in output gearing.
DQSW[2]	Write Control	Used for output and tristate logic at DQS only.
DYNDEL[7:0]	Write Control	Shifting of write clocks for specific DQS group, using 6:0 each step is approximately 25ps, 128 steps. Bit 7 is an invert (timing depends on input frequency). There is also a static control for this 8-bit setting, enabled with a memory cell.
DCNTL[6:0]	PIO Control	Original delay code from DDR DLL
DATAVALID[1]	Output Data	Status flag from DATAVALID logic, used to indicate when input data is captured in IOLOGIC and valid to core.
READ	For DQS_Strobe	Read signal for DDR memory interface
DQSI	For DQS_Strobe	Unshifted DQS strobe from input pad
PRMBDET	For DQS_Strobe	DQSI biased to go high when DQSI is tristate, goes to input logic block as well as core logic.
GSRN	Control from routing	Global Set/Reset

1. Signals available on left/right/top edges only.
2. Selected PIO.

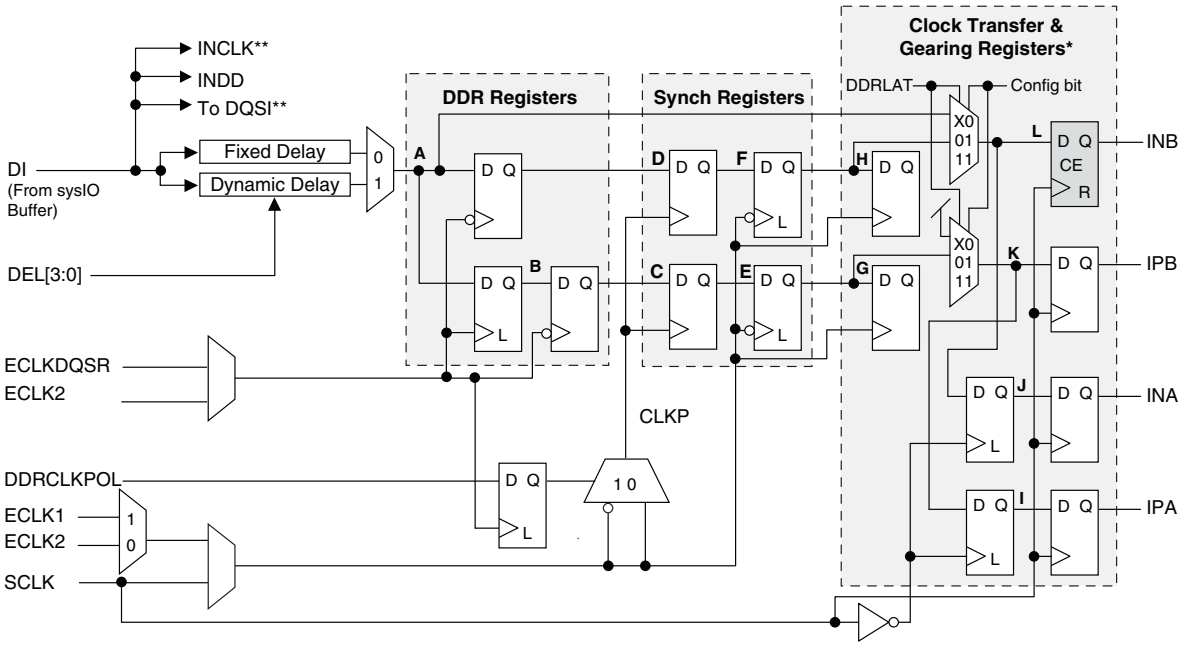
PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Input Register Block

The input register blocks for the PIOs, in the left, right and top edges, contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-33 shows the input register block for the left, right and top edges. The input register block for the bottom edge contains one element to register the input signal and no DDR registers. The following description applies to the input register block for PIOs in the left, right and top edges only.

Figure 2-33. Input Register Block for Left, Right and Top Edges



* Only on the left and right sides.
** Selected PIO.
Note: Simplified diagram does not show CE/SET/REST details.

Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysI/O buffers. The blocks on the left and right PIOs contain registers for SDR and full DDR operation. The topside PIO block is the same as the left and right sides except it does not support ODDRX2 gearing of output logic. ODDRX2 gearing is used in DDR3 memory interfaces.The PIO blocks on the bottom contain the SDR registers but do not support generic DDR.

Figure 2-34 shows the Output Register Block for PIOs on the left and right edges.

In SDR mode, OPOSA feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a Dtype or latch. In DDR mode, two of the inputs are fed into registers on the positive edge of the clock. At the next clock cycle, one of the registered outputs is also latched.

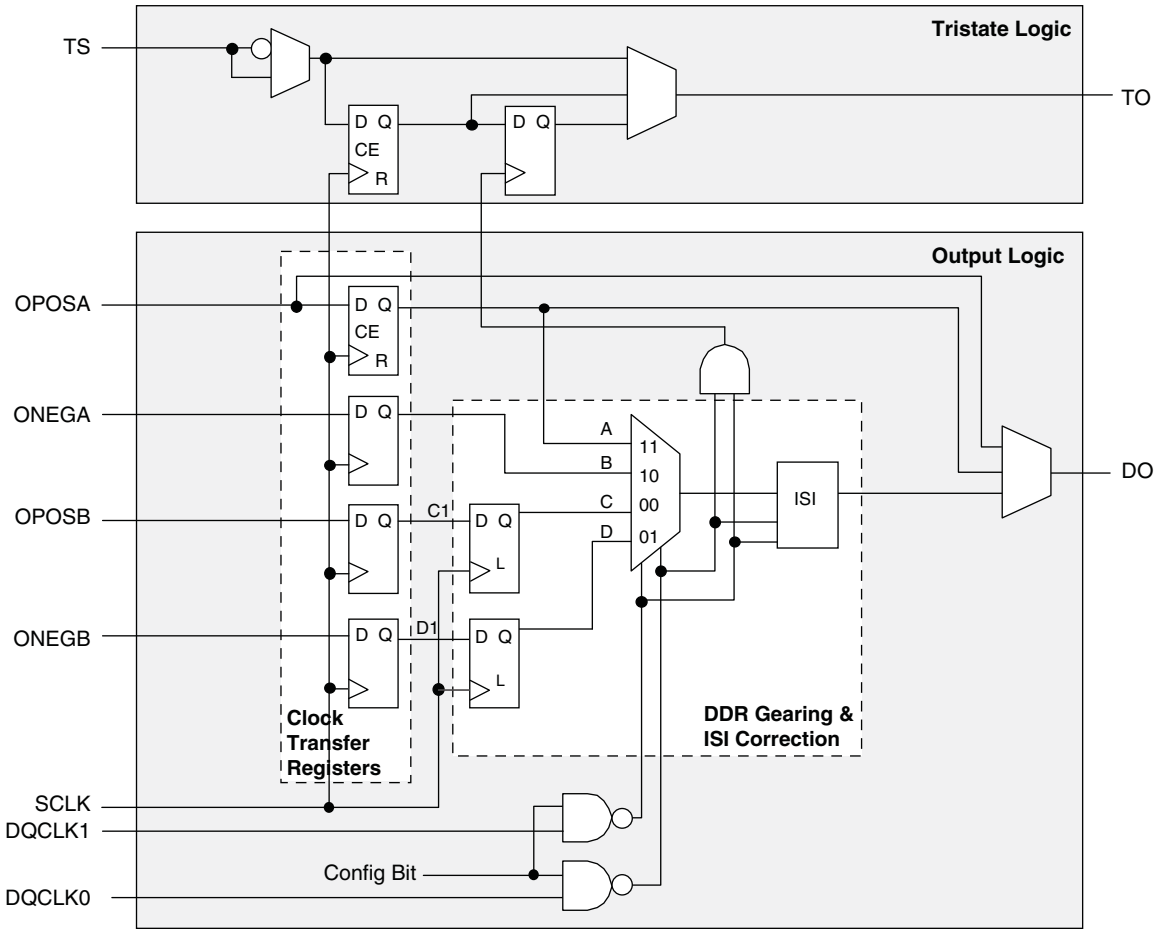
A multiplexer running off the same clock is used to switch the mux between the 11 and 01 inputs that will then feed the output.

A gearbox function can be implemented in the output register block that takes four data streams: OPOSA, ONEGA, OPOSB and ONEGB. All four data inputs are registered on the positive edge of the system clock and two of them are also latched. The data is then output at a high rate using a multiplexer that runs off the DQCLK0 and DQCLK1 clocks. DQCLK0 and DQCLK1 are used in this case to transfer data from the system clock to the edge clock domain. These signals are generated in the DQS Write Control Logic block. See Figure 2-37 for an overview of the DQS write control logic.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.

Further discussion on using the DQS strobe in this module is discussed in the DDR Memory section of this data sheet.

Figure 2-34. Output and Tristate Block for Left and Right Edges



Tristate Register Block

The tristate register block registers tri-state control signals from the core of the device before they are passed to the sysI/O buffers. The block contains a register for SDR operation and an additional register for DDR operation.

In SDR and non-gearing DDR modes, TS input feeds one of the flip-flops that then feeds the output. In DDRX2 mode, the register TS input is fed into another register that is clocked using the DQCLK0 and DQCLK1 signals. The output of this register is used as a tristate control.

ISI Calibration

The setting for Inter-Symbol Interference (ISI) cancellation occurs in the output register block. ISI correction is only available in the DDRX2 modes. ISI calibration settings exist once per output register block, so each I/O in a DQS-12 group may have a different ISI calibration setting.

The ISI block extends output signals at certain times, as a function of recent signal history. So, if the output pattern consists of a long strings of 0's to long strings of 1's, there are no delays on output signals. However, if there are quick, successive transitions from 010, the block will stretch out the binary 1. This is because the long trail of 0's will cause these symbols to interfere with the logic 1. Likewise, if there are quick, successive transitions from 101, the block will stretch out the binary 0. This block is controlled by a 3-bit delay control that can be set in the DQS control logic block.

For more information about this topic, please see the list of technical documentation at the end of this data sheet.

DLL Calibrated DQS Delay Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces, a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Delay block provides the required clock alignment for DDR memory interfaces.

The delay required for the DQS signal is generated by two dedicated DLLs (DDR DLL) on opposite side of the device. Each DLL creates DQS delays in its half of the device as shown in Figure 2-36. The DDR DLL on the left side will generate delays for all the DQS Strobe pins on Banks 0, 7 and 6 and DDR DLL on the right will generate delays for all the DQS pins on Banks 1, 2 and 3. The DDR DLL loop compensates for temperature, voltage and process variations by using the system clock and DLL feedback loop. DDR DLL communicates the required delay to the DQS delay block using a 7-bit calibration bus (DCNTL[6:0])

The DQS signal (selected PIOs only, as shown in Figure 2-35) feeds from the PAD through a DQS control logic block to a dedicated DQS routing resource. The DQS control logic block consists of DQS Read Control logic block that generates control signals for the read side and DQS Write Control logic that generates the control signals required for the write side. A more detailed DQS control diagram is shown in Figure 2-37, which shows how the DQS control blocks interact with the data paths.

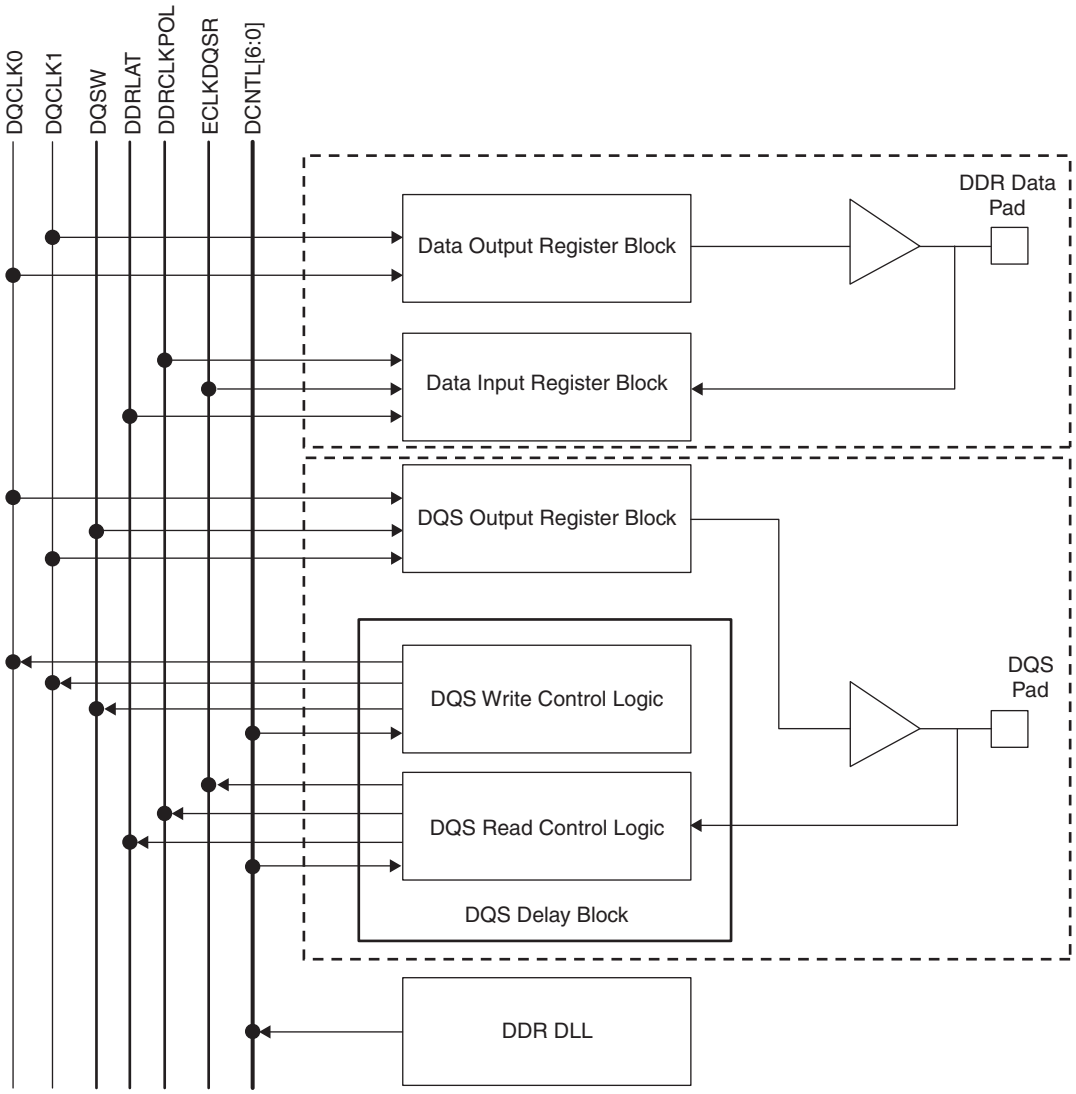
The DQS Read control logic receives the delay generated by the DDR DLL on its side and delays the incoming DQS signal by 90 degrees. This delayed ECLKDQSR is routed to 10 or 11 DQ pads covered by that DQS signal. This block also contains a polarity control logic that generates a DDRCLKPOL signal, which controls the polarity of the clock to the sync registers in the input register blocks. The DQS Read control logic also generates a DDRLAT signal that is in the input register block to transfer data from the first set of DDR register to the second set of DDR registers when using the DDRX2 gearbox mode for DDR3 memory interface.

The DQS Write control logic block generates the DQCLK0 and DQCLK1 clocks used to control the output gearing in the Output register block which generates the DDR data output and the DQS output. They are also used to control the generation of the DQS output through the DQS output register block. In addition to the DCNTL [6:0] input from the DDR DLL, the DQS Write control block also uses a Dynamic Delay DYN DEL [7:0] attribute which is used to further delay the DQS to accomplish the write leveling found in DDR3 memory. Write leveling is controlled by the DDR memory controller implementation. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock. This will generate the DQSW signal used to generate the DQS output in the DQS output register block.

Figure 2-36 and Figure 2-37 show how the DQS transition signals that are routed to the PIOs.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.

Figure 2-37. DQS Local Bus



Polarity Control Logic

In a typical DDR Memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the READ cycle) is unknown. The LatticeECP3 family contains dedicated circuits to transfer data between these domains. A clock polarity selector is used to prevent set-up and hold violations at the domain transfer between DQS (delayed) and the system clock. This changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each READ cycle for the correct clock polarity.

Prior to the READ operation in DDR memories, DQS is in tristate (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit detects the first DQS rising edge after the preamble state. This signal is used to control the polarity of the clock to the synchronizing registers.

DDR3 Memory Support

LatticeECP3 supports the read and write leveling required for DDR3 memory interfaces.

Read leveling is supported by the use of the DDRCLKPOL and the DDRLAT signals generated in the DQS Read Control logic block. These signals dynamically control the capture of the data with respect to the DQS at the input register block.

LVDS25E

The top and bottom sides of LatticeECP3 devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3-1 is one possible solution for point-to-point signals.

Figure 3-1. LVDS25E Output Termination Example

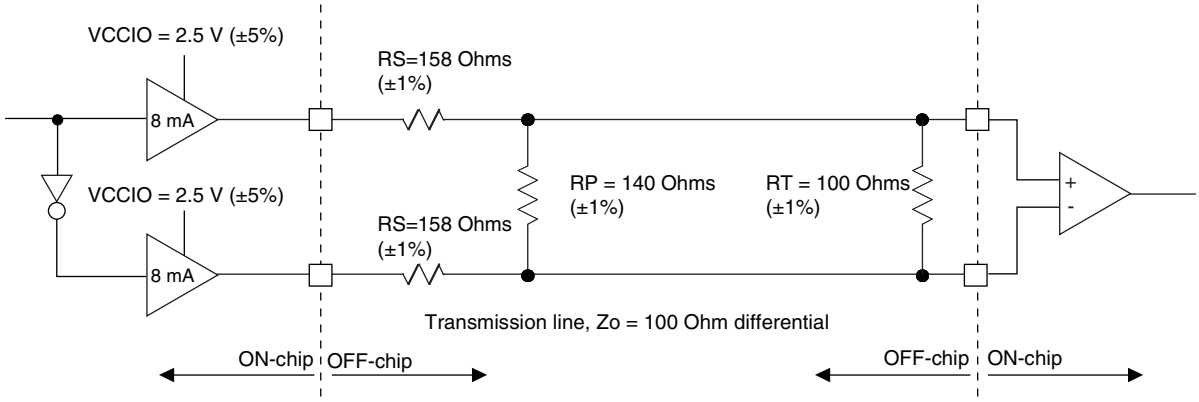


Table 3-1. LVDS25E DC Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/–5%)	2.50	V
Z_{OUT}	Driver Impedance	20	Ω
R_S	Driver Series Resistor (+/–1%)	158	Ω
R_P	Driver Parallel Resistor (+/–1%)	140	Ω
R_T	Receiver Termination (+/–1%)	100	Ω
V_{OH}	Output High Voltage	1.43	V
V_{OL}	Output Low Voltage	1.07	V
V_{OD}	Output Differential Voltage	0.35	V
V_{CM}	Output Common Mode Voltage	1.25	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	6.03	mA

LVCMOS33D

All I/O banks support emulated differential I/O using the LVCMOS33D I/O type. This option, along with the external resistor network, provides the system designer the flexibility to place differential outputs on an I/O bank with 3.3 V V_{CCIO}. The default drive current for LVCMOS33D output is 12 mA with the option to change the device strength to 4 mA, 8 mA, 16 mA or 20 mA. Follow the LVCMOS33 specifications for the DC characteristics of the LVCMOS33D.

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-150EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.8	—	4.2	—	4.6	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-70EA/95EA	1.4	—	1.6	—	1.8	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70EA/95EA	1.3	—	1.5	—	1.7	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-35EA	—	3.7	—	4.1	—	4.5	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-35EA	1.2	—	1.4	—	1.6	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-35EA	1.3	—	1.4	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-35EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-17EA	—	3.5	—	3.9	—	4.3	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-17EA	1.3	—	1.5	—	1.6	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-17EA	1.3	—	1.4	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-17EA	—	500	—	420	—	375	MHz
General I/O Pin Parameters Using Dedicated Clock Input Primary Clock with PLL with Clock Injection Removal Setting[2]									
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-150EA	—	3.3	—	3.6	—	39	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.7	—	0.8	—	0.9	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.6	—	1.8	—	2.0	—	ns
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	—	0.0	—	0.0	—	0.0	ns
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.3	—	3.5	—	3.8	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.7	—	0.8	—	0.9	—	ns

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-35EA	683	—	688	—	690	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-35EA	683	—	688	—	690	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-17EA	683	—	688	—	690	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-17EA	683	—	688	—	690	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX1 Output with Clock and Data Aligned at Pin (GDDRX1_TX.SCLK.Aligned)[10]									
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-150EA	—	335	—	338	—	341	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-150EA	—	335	—	338	—	341	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-70EA/95EA	—	339	—	343	—	347	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-70EA/95EA	—	339	—	343	—	347	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-35EA	—	322	—	320	—	321	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-35EA	—	322	—	320	—	321	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-17EA	—	322	—	320	—	321	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-17EA	—	322	—	320	—	321	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX1 Output with Clock and Data (<10 Bits Wide) Centered at Pin (GDDRX1_TX.DQS.Centered)[10]									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-35EA	670	—	675	—	676	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-35EA	670	—	675	—	676	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-17EA	670	—	670	—	670	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-17EA	670	—	670	—	670	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX2 Output with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDRX2_TX.Aligned)									
Left and Right Sides									
$t_{DIBGDDR}$	Data Invalid Before Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
$t_{DIAGDDR}$	Data Invalid After Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	500	—	420	—	375	MHz
Generic DDRX2 Output with Clock and Data (>10 Bits Wide) Centered at Pin Using DQSDLL (GDDRX2_TX.DQSDLL.Centered)[11]									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	All ECP3EA Devices	400	—	400	—	431	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	All ECP3EA Devices	400	—	400	—	432	—	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz

Figure 3-14. Jitter Transfer – 3.125 Gbps

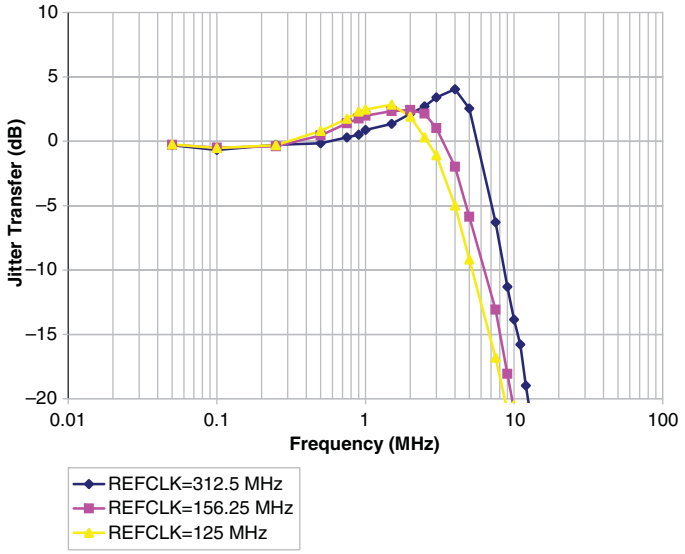
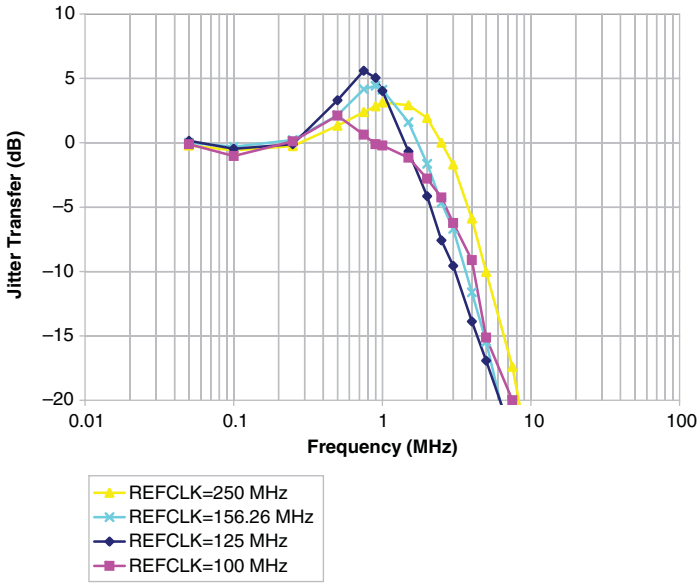


Figure 3-15. Jitter Transfer – 2.5 Gbps



XAUI/Serial Rapid I/O Type 3/CPRI LV E.30 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-13. Transmit

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[2, 3, 4]	Output data deterministic jitter		—	—	0.17	UI
J_{TX_TJ}[1, 2, 3, 4]	Total output data jitter		—	—	0.35	UI

1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Values are measured at 2.5 Gbps.

Table 3-14. Receive and Jitter Tolerance

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[1, 2, 3]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
J_{RX_RJ}[1, 2, 3]	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
J_{RX_SJ}[1, 2, 3]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
J_{RX_TJ}[1, 2, 3]	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

HDMI (High-Definition Multimedia Interface) Electrical and Timing Characteristics

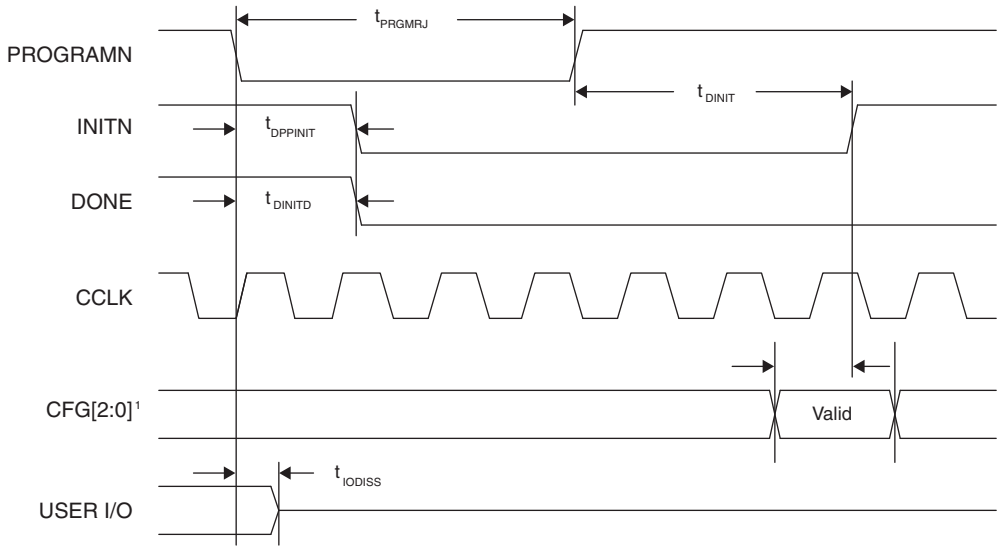
AC and DC Characteristics

Table 3-22. Transmit and Receive[1, 2]

Symbol	Description	Spec. Compliance		Units
		Min. Spec.	Max. Spec.	
Transmit				
Intra-pair Skew		—	75	ps
Inter-pair Skew		—	800	ps
TMDS Differential Clock Jitter		—	0.25	UI
Receive				
R_T	Termination Resistance	40	60	Ohms
V_{ICM}	Input AC Common Mode Voltage (50-Ohm Setting)	—	50	mV
TMDS Clock Jitter	Clock Jitter Tolerance	—	0.25	UI

1. Output buffers must drive a translation device. Max. speed is 2 Gbps. If translation device does not modify rise/fall time, the maximum speed is 1.5 Gbps.
2. Input buffers must be AC coupled in order to support the 3.3 V common mode. Generally, HDMI inputs are terminated by an external cable equalizer before data/clock is forwarded to the LatticeECP3 device.

Figure 3-26. Configuration from PROGRAMN Timing



1. The CFG pins are normally static (hard wired)

Figure 3-27. Wake-Up Timing

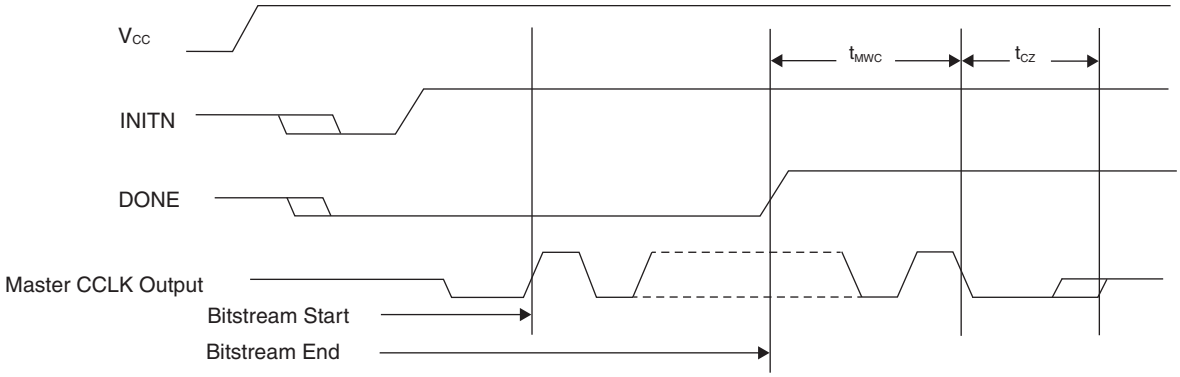


Figure 3-28. Master SPI Configuration Waveforms

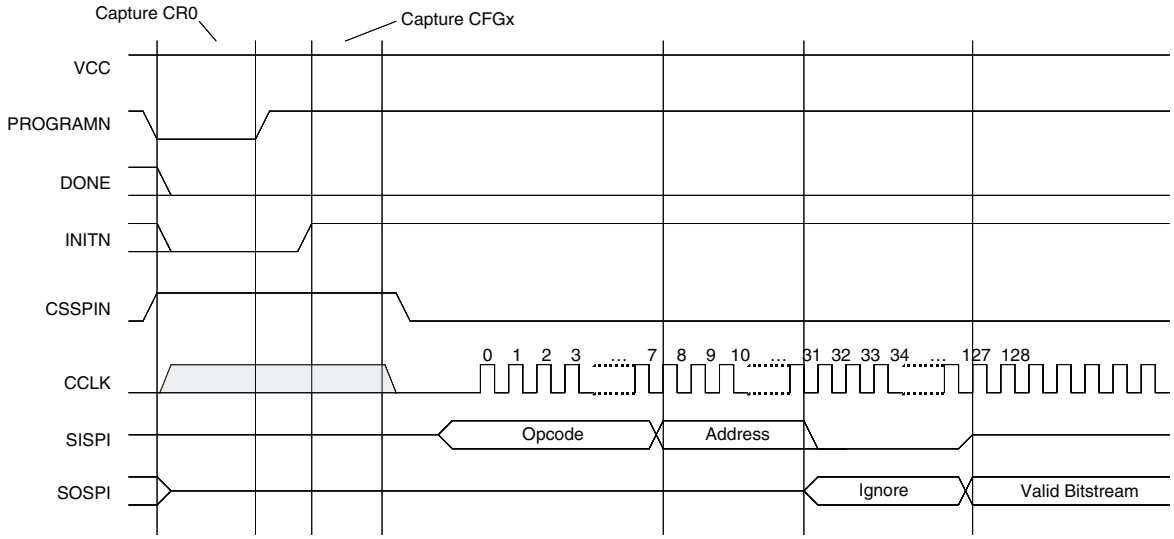
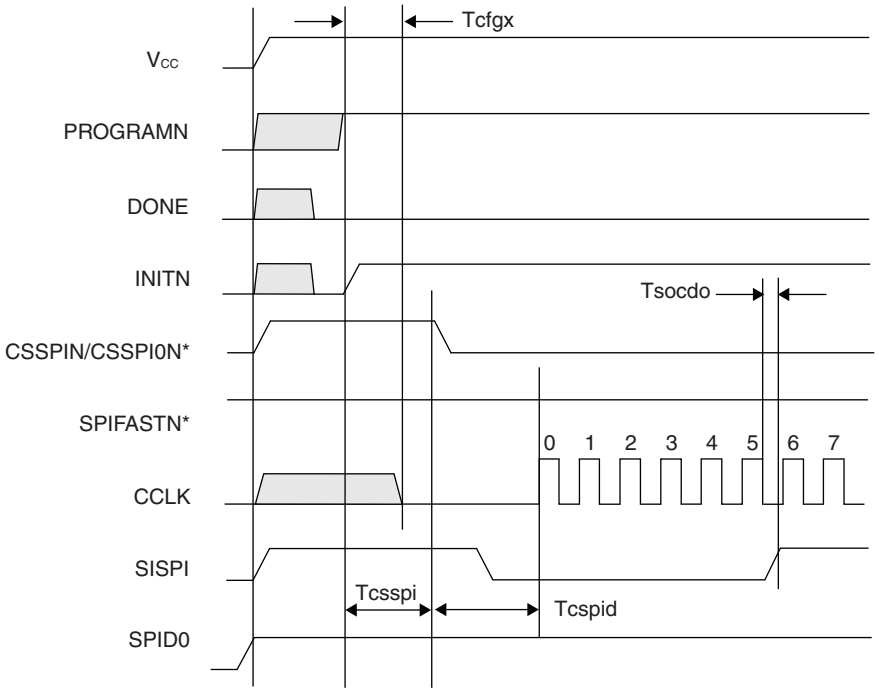


Figure 3-29. Master SPI POR Waveforms



Signal Descriptions

Signal Name	I/O	Description
General Purpose		
P[Edge] [Row/Column Number]_[A/B]	I/O	[Edge] indicates the edge of the device on which the pad is located. Valid edge designations are L (Left), B (Bottom), R (Right), T (Top). [Row/Column Number] indicates the PFU row or the column of the device on which the PIC exists. When Edge is T (Top) or B (Bottom), only need to specify Column Number. When Edge is L (Left) or R (Right), only need to specify Row Number. [A/B] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with special function pins. These pins, when not used as special purpose pins, can be programmed as I/Os for user logic. During configuration the user-programmable I/Os are tri-stated with an internal pull-up resistor enabled. If any pin is not used (or not bonded to a package pin), it is also tri-stated with an internal pull-up resistor enabled after configuration.
P[Edge][Row Number]E_[A/B/C/D]	I	These general purpose signals are input-only pins and are located near the PLLs.
GSRN	I	Global RESET signal (active low). Any I/O pin can be GSRN.
NC	—	No connect.
RESERVED	—	This pin is reserved and should not be connected to anything on the board.
GND	—	Ground. Dedicated pins.
V_{CC}	—	Power supply pins for core logic. Dedicated pins.
V_{CCAUX}	—	Auxiliary power supply pin. This dedicated pin powers all the differential and referenced input buffers.
V_{CCIOx}	—	Dedicated power supply pins for I/O bank x.
V_{CCA}	—	SERDES, transmit, receive, PLL and reference clock buffer power supply. All V_{CCA} supply pins must always be powered to the recommended operating voltage range. If no SERDES channels are used, connect V_{CCA} to V_{CC}.
$V_{CCPLL\_[LOC]}$	—	General purpose PLL supply pins where LOC=L (left) or R (right).
V_{REF1_x}, V_{REF2_x}	—	Reference supply pins for I/O bank x. Pre-determined pins in each bank are assigned as V_{REF} inputs. When not used, they may be used as I/O pins.
VTTx	—	Power supply for on-chip termination of I/Os.
XRES[1]	—	10 kOhm +/-1% resistor must be connected between this pad and ground.
PLL, DLL and Clock Functions		
[LOC][num]_GPLL[T, C]_IN_[index]	I	General Purpose PLL (GPLL) input pads: LUM, LLM, RUM, RLM, num = row from center, T = true and C = complement, index A,B,C...at each side.
[LOC][num]_GPLL[T, C]_FB_[index]	I	Optional feedback GPLL input pads: LUM, LLM, RUM, RLM, num = row from center, T = true and C = complement, index A,B,C...at each side.
[LOC]0_GDLLT_IN_[index][2]	I/O	General Purpose DLL (GDLL) input pads where LOC=RUM or LUM, T is True Complement, index is A or B.
[LOC]0_GDLLT_FB_[index][2]	I/O	Optional feedback GDLL input pads where LOC=RUM or LUM, T is True Complement, index is A or B.
PCLK[T, C][n:0]_[3:0][2]	I/O	Primary Clock pads, T = true and C = complement, n per side, indexed by bank and 0, 1, 2, 3 within bank.

Pin Information Summary

Pin Information Summary		ECP3-17EA			ECP3-35EA			ECP3-70EA		
Pin Type		256 ftBGA	328 csBGA	484 fpBGA	256 ftBGA	484 fpBGA	672 fpBGA	484 fpBGA	672 fpBGA	1156 fpBGA
General Purpose Inputs/Outputs per Bank	Bank 0	26	20	36	26	42	48	42	60	86
	Bank 1	14	10	24	14	36	36	36	48	78
	Bank 2	6	7	12	6	24	24	24	34	36
	Bank 3	18	12	44	16	54	59	54	59	86
	Bank 6	20	11	44	18	63	61	63	67	86
	Bank 7	19	26	32	19	36	42	36	48	54
	Bank 8	24	24	24	24	24	24	24	24	24
General Purpose Inputs per Bank	Bank 0	0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0	0
	Bank 2	2	2	2	2	4	4	4	8	8
	Bank 3	0	0	0	2	4	4	4	12	12
	Bank 6	0	0	0	2	4	4	4	12	12
	Bank 7	4	4	4	4	4	4	4	8	8
	Bank 8	0	0	0	0	0	0	0	0	0
General Purpose Outputs per Bank	Bank 0	0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0	0
	Bank 2	0	0	0	0	0	0	0	0	0
	Bank 3	0	0	0	0	0	0	0	0	0
	Bank 6	0	0	0	0	0	0	0	0	0
	Bank 7	0	0	0	0	0	0	0	0	0
	Bank 8	0	0	0	0	0	0	0	0	0
Total Single-Ended User I/O		133	116	222	133	295	310	295	380	490
VCC		6	16	16	6	16	32	16	32	32
VCCAUX		4	5	8	4	8	12	8	12	16
VTT		4	7	4	4	4	4	4	4	8
VCCA		4	6	4	4	4	8	4	8	16
VCCPLL		2	2	4	2	4	4	4	4	4
VCCIO	Bank 0	2	3	2	2	2	4	2	4	4
	Bank 1	2	3	2	2	2	4	2	4	4
	Bank 2	2	2	2	2	2	4	2	4	4
	Bank 3	2	3	2	2	2	4	2	4	4
	Bank 6	2	3	2	2	2	4	2	4	4
	Bank 7	2	3	2	2	2	4	2	4	4
	Bank 8	1	2	2	1	2	2	2	2	2
VCCJ		1	1	1	1	1	1	1	1	1
TAP		4	4	4	4	4	4	4	4	4
GND, GNDIO		51	126	98	51	98	139	98	139	233
NC		0	0	73	0	0	96	0	0	238
Reserved[1]		0	0	2	0	2	2	2	2	2
SERDES		26	18	26	26	26	26	26	52	78
Miscellaneous Pins		8	8	8	8	8	8	8	8	8
Total Bonded Pins		256	328	484	256	484	672	484	672	1156

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-70EA-6FN484C	1.2 V	–6	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-7FN484C	1.2 V	–7	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-8FN484C	1.2 V	–8	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-6LFN484C	1.2 V	–6	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-7LFN484C	1.2 V	–7	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-8LFN484C	1.2 V	–8	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-6FN672C	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-7FN672C	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-8FN672C	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-6LFN672C	1.2 V	–6	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-7LFN672C	1.2 V	–7	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-8LFN672C	1.2 V	–8	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-6FN1156C	1.2 V	–6	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-7FN1156C	1.2 V	–7	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-8FN1156C	1.2 V	–8	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-6LFN1156C	1.2 V	–6	LOW	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-7LFN1156C	1.2 V	–7	LOW	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-8LFN1156C	1.2 V	–8	LOW	Lead-Free fpBGA	1156	COM	67

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-95EA-6FN484C	1.2 V	–6	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7FN484C	1.2 V	–7	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8FN484C	1.2 V	–8	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6LFN484C	1.2 V	–6	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7LFN484C	1.2 V	–7	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8LFN484C	1.2 V	–8	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6FN672C	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7FN672C	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8FN672C	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6LFN672C	1.2 V	–6	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7LFN672C	1.2 V	–7	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8LFN672C	1.2 V	–8	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6FN1156C	1.2 V	–6	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7FN1156C	1.2 V	–7	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8FN1156C	1.2 V	–8	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-6LFN1156C	1.2 V	–6	LOW	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7LFN1156C	1.2 V	–7	LOW	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8LFN1156C	1.2 V	–8	LOW	Lead-Free fpBGA	1156	COM	92

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672C	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672C	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672C	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6LFN672C	1.2 V	–6	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7LFN672C	1.2 V	–7	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8LFN672C	1.2 V	–8	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156C	1.2 V	–6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156C	1.2 V	–7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156C	1.2 V	–8	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-6LFN1156C	1.2 V	–6	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7LFN1156C	1.2 V	–7	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8LFN1156C	1.2 V	–8	LOW	Lead-Free fpBGA	1156	COM	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672CTW[1]	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672CTW[1]	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672CTW[1]	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156CTW[1]	1.2 V	–6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156CTW[1]	1.2 V	–7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156CTW[1]	1.2 V	–8	STD	Lead-Free fpBGA	1156	COM	149

1. Note: Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.
   - The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.
   - The SERDES XRES pin on the TW device passes CDM testing at 250 V.